

HSC119

Silicon Epitaxial Planar Diode for High Speed Switching

REJ03G0188-0100Z

(Previous: ADE-208-615)

Rev.1.00 Mar.22.2004

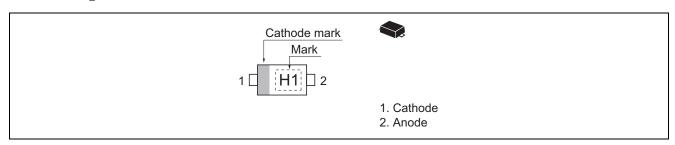
Features

- Low capacitance. (C = 2.0 pF max)
- Short reverse recovery time. $(t_{rr} = 3.0 \text{ ns max})$
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code	
HSC119	H1	UFP	

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Peak reverse voltage	V_{RM}	85	V	
Reverse voltage	V _R	80	V	
Peak forward current	I _{FM}	300	mA	
Non-Repetitive peak forward surge current	I _{FSM} *1	4	А	
Average rectified current	Io	100	mA	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

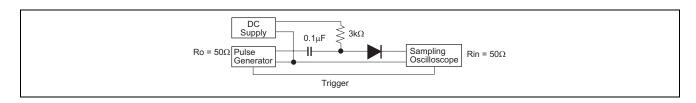
Note: 1. Within $1\mu s$ forward surge current.

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V_{F1}	_	_	8.0	V	I _F = 10 mA
	V _{F2}	_	_	1.2		I _F = 100 mA
Reverse current	I _R	_	_	0.1	μΑ	V _R = 80 V
Capacitance	С	_	_	2.0	pF	V _R = 0 V, f = 1 MHz
Reverse recovery time*1	t _{rr}	_	_	3.0	ns	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 50 \Omega$

Note: 1. Reverse recovery time test circuit



Main Characteristics

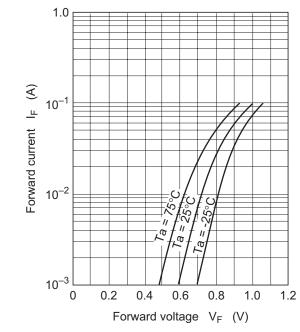


Fig.1 Forward current vs. Forward voltage

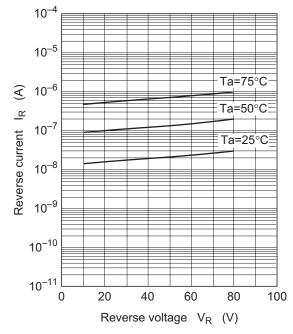
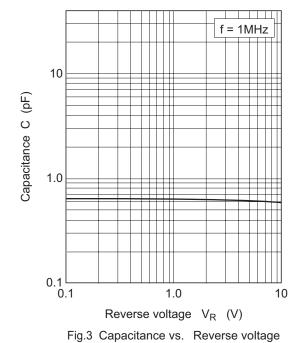
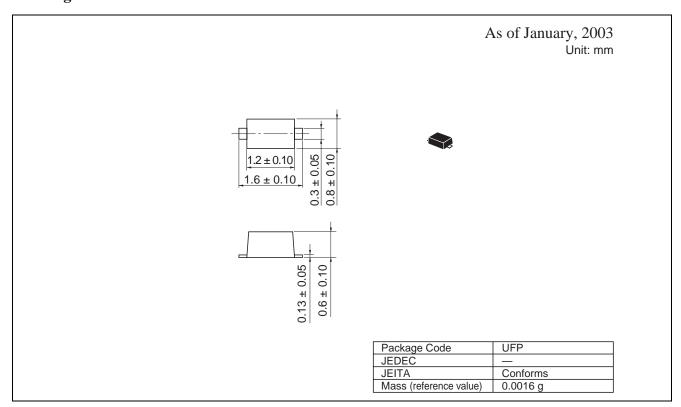


Fig.2 Reverse current vs. Reverse voltage



Package Dimensions



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